HIGH DIODE

T055NE8NTH

RoHS COMPLIANT

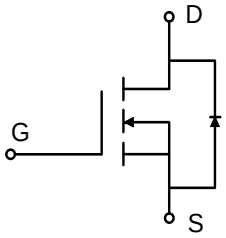
85V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
85V	4mΩ@10V	125A

TO-263-2L

Schematic diagram



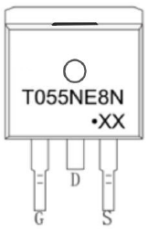
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Industrial Power Supply
- Load Switch

MARKING



T055NE8N = Device Code
XX = Date Code
Solid Dot = Green Indicater

ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	85	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1]	T_C = 25℃	I_D	125	A
Pulsed Drain Current[2]		I_{DM}	500	A
Single Pulsed Avalanche Current[3]		I_{AS}	47	A
Single Pulsed Avalanche Energy[3]		E_{AS}	552	mJ
Power Dissipation[5]	T_C = 25℃	P_D	162	W
Thermal Resistance from Junction to Ambient[6]		$R_{\theta JA}$	58	℃/W
Thermal Resistance from Junction to Case		$R_{\theta JC}$	0.77	℃/W
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-55~ +150	℃

Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	85			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[4]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 10A		4	5.5	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 10V, I_D = 10A	60			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 40V, V_{GS} = 0V, f = 1MHz		4274		pF
Output Capacitance	C_{oss}			655		
Reverse Transfer Capacitance	C_{rss}			28		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		1.6		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = 45V, V_{GS} = 10V, I_D = 20A		60		nC
Gate-source Charge	Q_{gs}			28		
Gate-drain Charge	Q_{gd}			17		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 45V, V_{GS} = 10V, R_L = 2Ω R_G = 3Ω		25		ns
Turn-on Rise Time	t_r			21		
Turn-off Delay Time	$t_{d(off)}$			53		
Turn-off Fall Time	t_f			24		
Source - Drain Diode Characteristics						
Diode Forward Voltage[4]	V_{SD}	V_{GS} = 0V, I_S = 10A	0.5		1.4	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

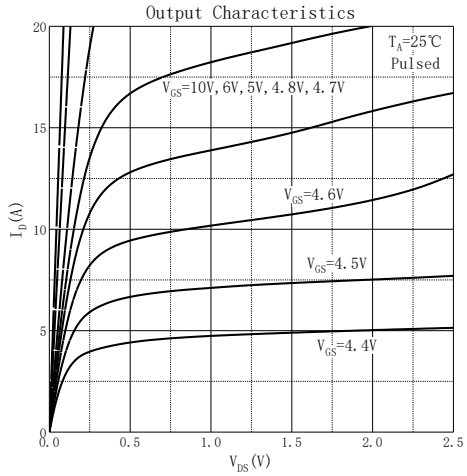
3.E_{AS} condition: V_{DD} = 25V,V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°℃.

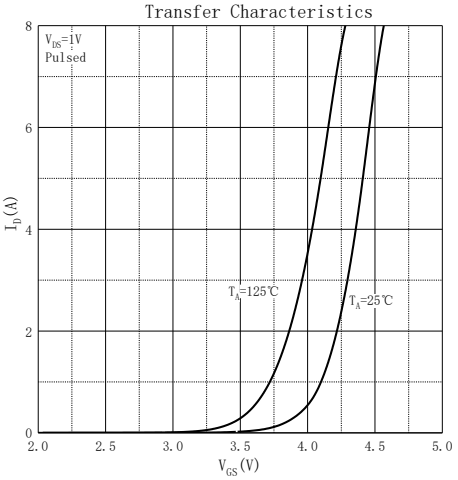
4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

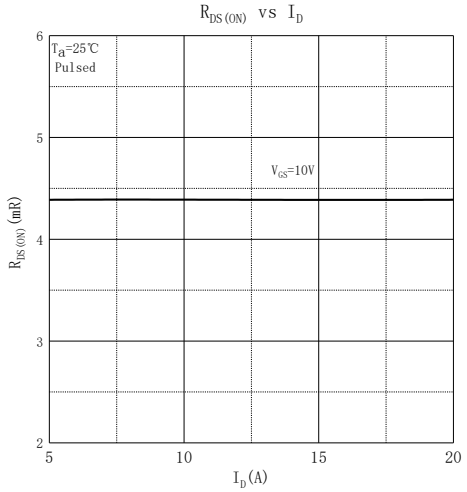
5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

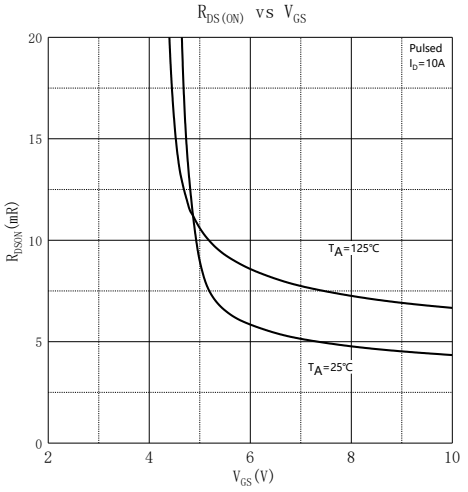
6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

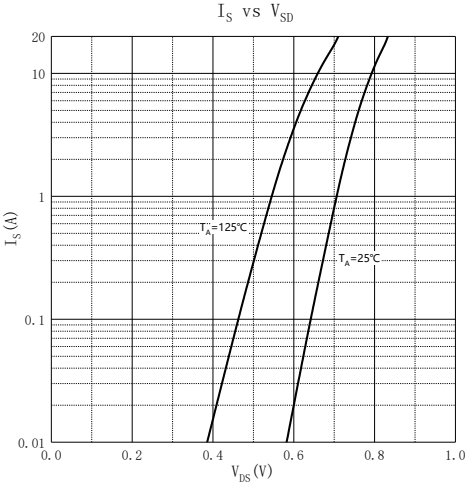
Typical Characteristics

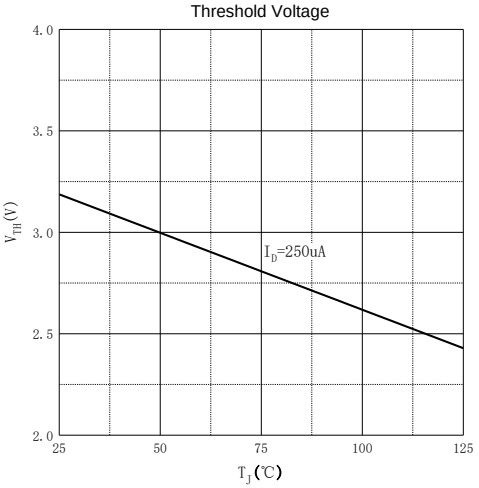












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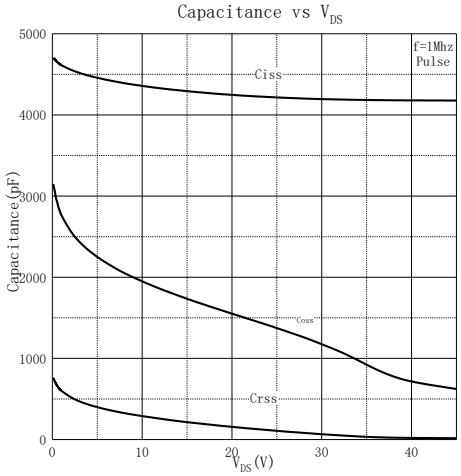

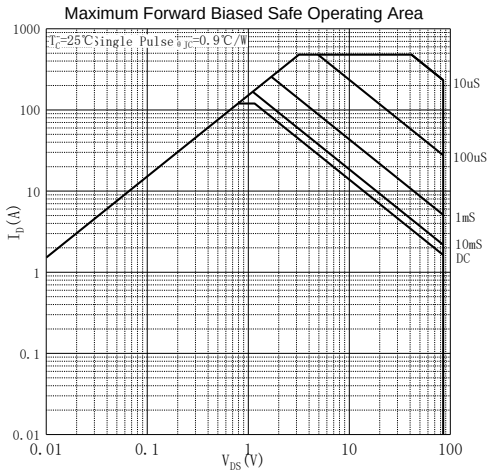

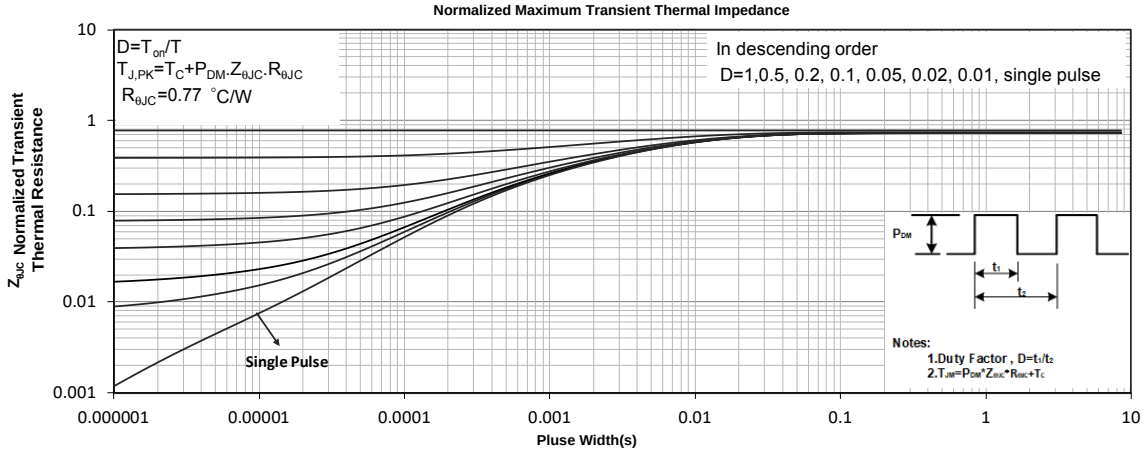

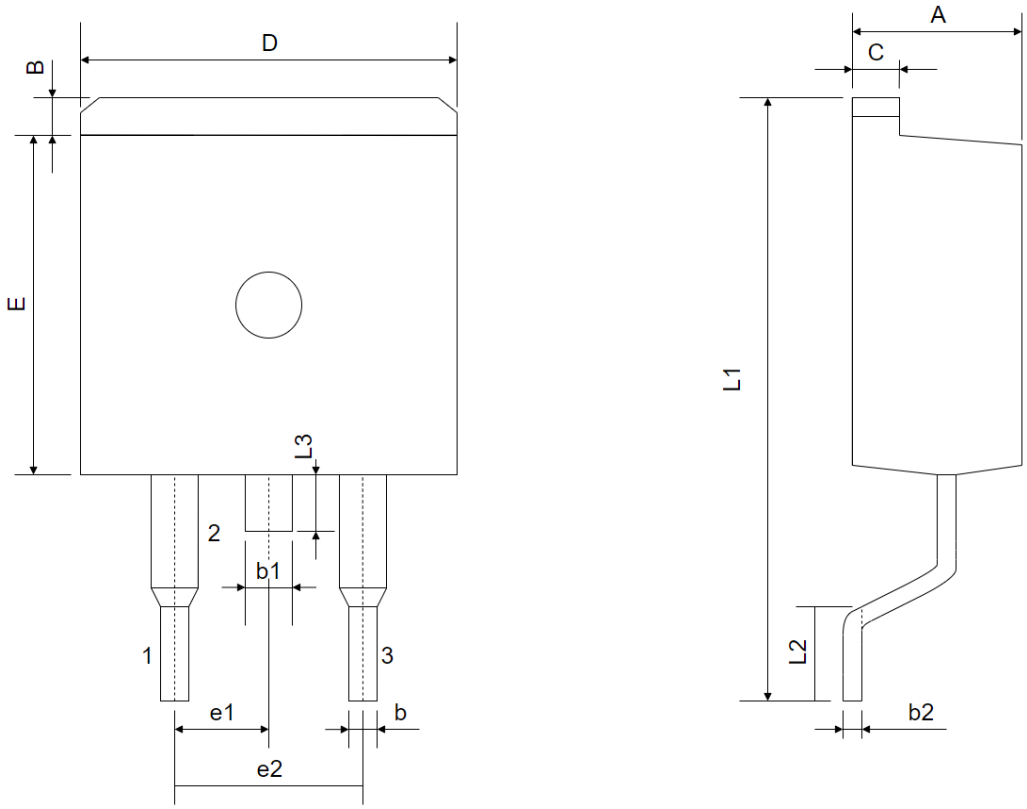

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
B	1.000	1.400	0.039	0.055
b	0.700	0.900	0.028	0.035
b1	1.150	1.40	0.045	0.053
b2	0.400	0.600	0.016	0.024
C	1.200	1.400	0.047	0.055
D	9.680	10.200	0.381	0.402
E	9.000	9.400	0.354	0.370
e1	2.340	2.740	0.092	0.108
e2	4.880	5.280	0.192	0.208
L1	14.800	16.000	0.582	0.630
L2	2.100	2.840	0.083	0.112
L3	1.100	1.600	0.043	0.063